

NPN 9 GHz wideband transistor

BFG520; BFG520/X; BFG520/XR

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

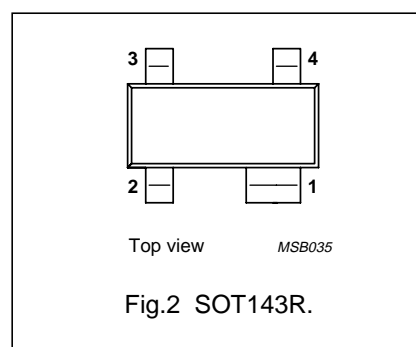
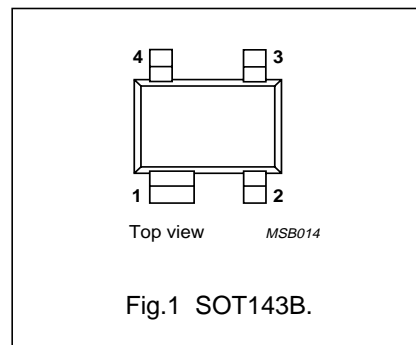
DESCRIPTION

NPN silicon planar epitaxial transistors, intended for applications in the RF frontend in the GHz range, such as analog and digital cellular telephones, cordless telephones (CT1, CT2, DECT, etc.), radar detectors, pagers and satellite TV tuners (SATV) and repeater amplifiers in fibre-optic systems.

The transistors are encapsulated in 4-pin, dual-emitter plastic SOT143 and SOT143R envelopes.

PINNING

PIN	DESCRIPTION
BFG520 (Fig.1) Code: %MF	
1	collector
2	base
3	emitter
4	emitter
BFG520/X (Fig.1) Code: %ML	
1	collector
2	emitter
3	base
4	emitter
BFG520/XR (Fig.2) Code: %MP	
1	collector
2	emitter
3	base
4	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	DC collector current		–	–	70	mA
P_{tot}	total power dissipation	up to $T_s = 88\text{ °C}$; note 1	–	–	300	mW
h_{FE}	DC current gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $T_j = 25\text{ °C}$	60	120	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 6\text{ V}$; $f = 1\text{ MHz}$	–	0.3	–	pF
f_T	transition frequency	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	19	–	dB
		$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	13	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	17	18	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 5\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.1	1.6	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.6	2.1	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 5\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	1.9	–	dB

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	70	mA
P_{tot}	total power dissipation	up to $T_s = 88\text{ °C}$; note 1	–	300	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	175	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 88\text{ °C}$; note 1	290 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 6\text{ V}$	–	–	50	nA
h_{FE}	DC current gain	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}$	60	120	250	
C_e	emitter capacitance	$I_C = I_C = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	1	–	pF
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = 6\text{ V}; f = 1\text{ MHz}$	–	0.6	–	pF
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 6\text{ V}; f = 1\text{ MHz}$	–	0.3	–	pF
f_T	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; f = 1\text{ GHz};$ $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; f = 900\text{ MHz};$ $T_{amb} = 25\text{ °C}$	–	19	–	dB
		$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; f = 2\text{ GHz};$ $T_{amb} = 25\text{ °C}$	–	13	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; f = 900\text{ MHz};$ $T_{amb} = 25\text{ °C}$	17	18	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}; I_C = 5\text{ mA}; V_{CE} = 6\text{ V};$ $f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	1.1	1.6	dB
		$\Gamma_s = \Gamma_{opt}; I_C = 20\text{ mA}; V_{CE} = 6\text{ V};$ $f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	1.6	2.1	dB
		$\Gamma_s = \Gamma_{opt}; I_C = 5\text{ mA}; V_{CE} = 6\text{ V};$ $f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	1.9	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; R_L = 50\text{ }\Omega;$ $f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	17	–	dBm
ITO	third order intercept point	note 2	–	26	–	dBm
V_o	output voltage	note 3	–	275	–	mV
d_2	second order intermodulation distortion	$I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; V_o = 75\text{ mV};$ $T_{amb} = 25\text{ °C}; f_{(p+q)} = 810\text{ MHz}$	–	–50	–	dB

Notes

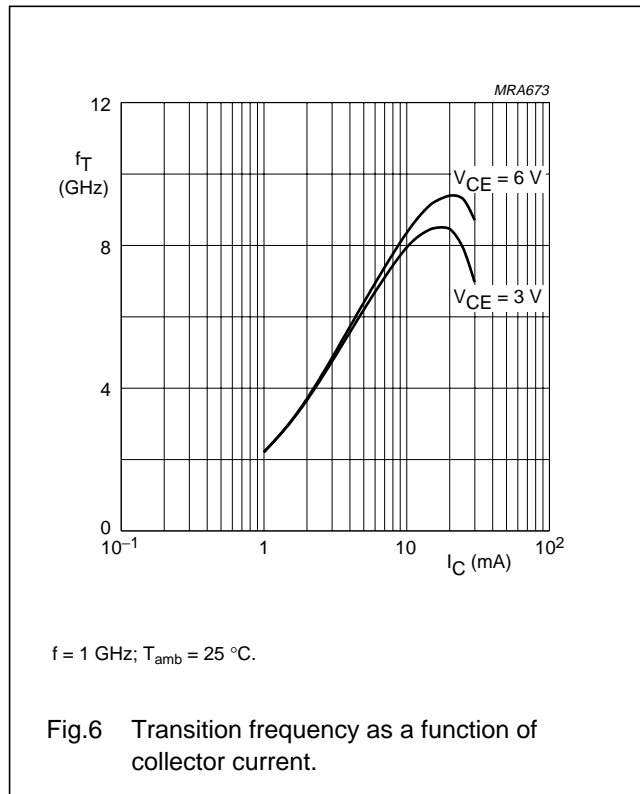
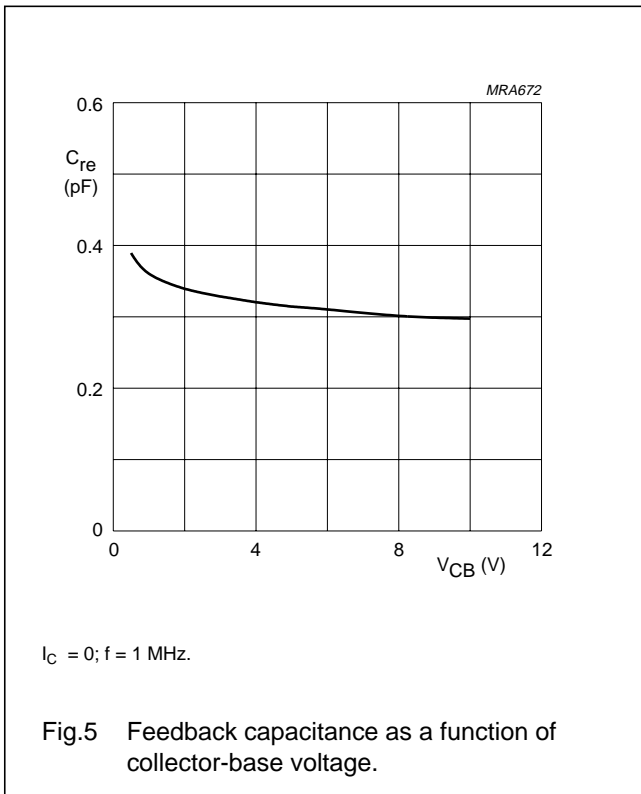
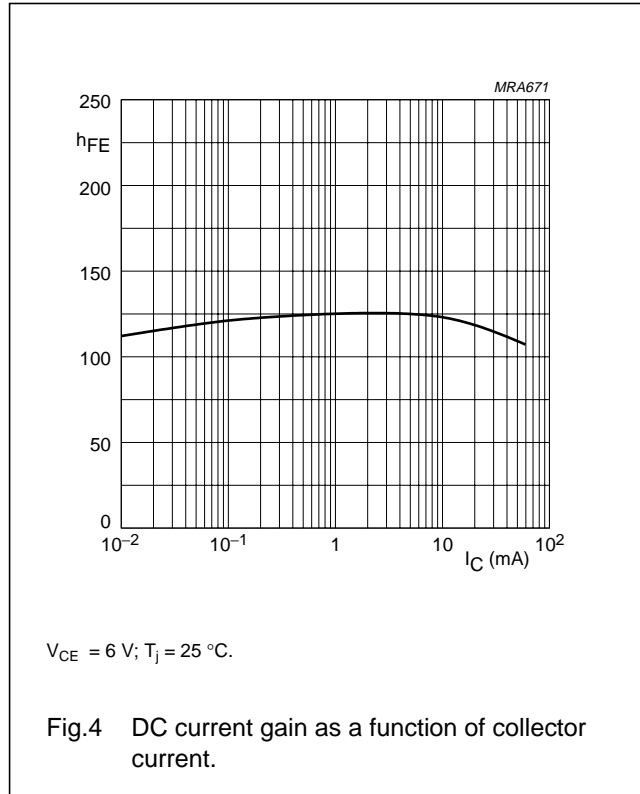
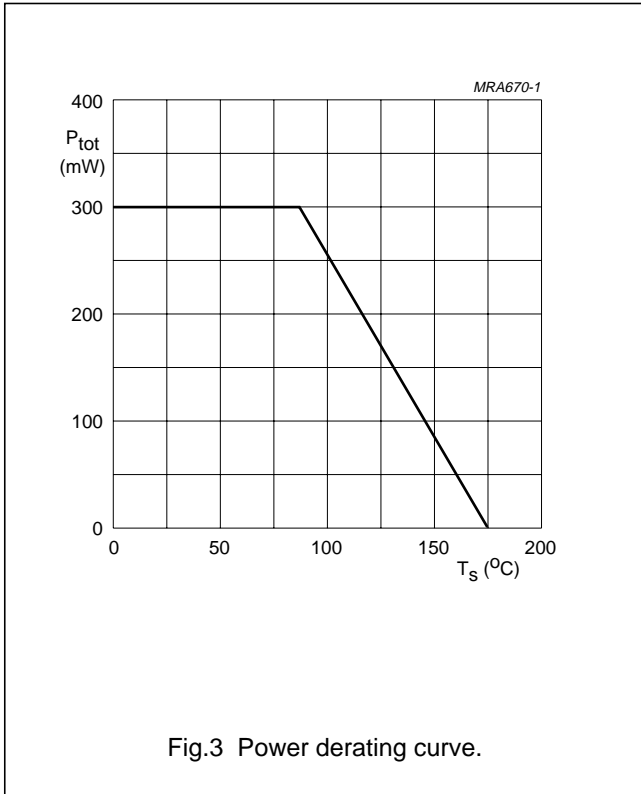
1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \left(\frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \right) \text{dB.}$$

2. $I_C = 20\text{ mA}; V_{CE} = 6\text{ V}; R_L = 50\text{ }\Omega; f = 900\text{ MHz}; T_{amb} = 25\text{ °C};$
 $f_p = 900\text{ MHz}; f_q = 902\text{ MHz};$
measured at $f_{(2p-q)} = 898\text{ MHz}$ and $f_{(2q-p)} = 904\text{ MHz}.$
3. $d_{im} = -60\text{ dB (DIN 45004B)};$
 $V_p = V_o; V_q = V_o - 6\text{ dB}; V_r = V_o - 6\text{ dB};$
 $f_p = 795.25\text{ MHz}; f_q = 803.25\text{ MHz}; f_r = 805.25\text{ MHz};$
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$

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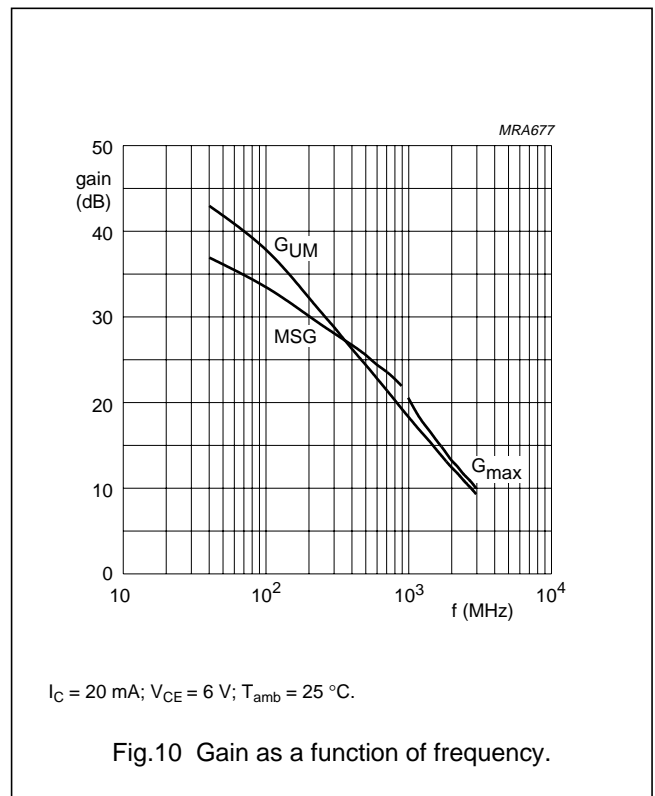
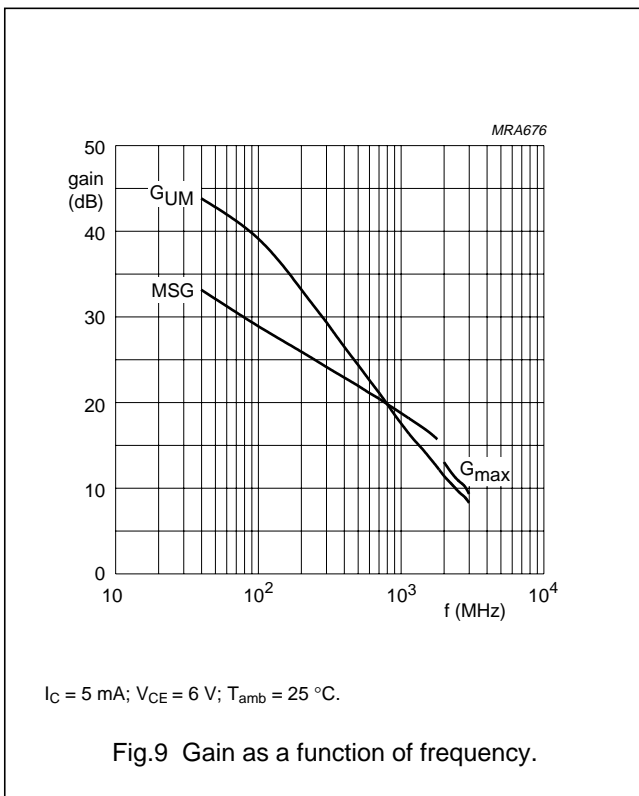
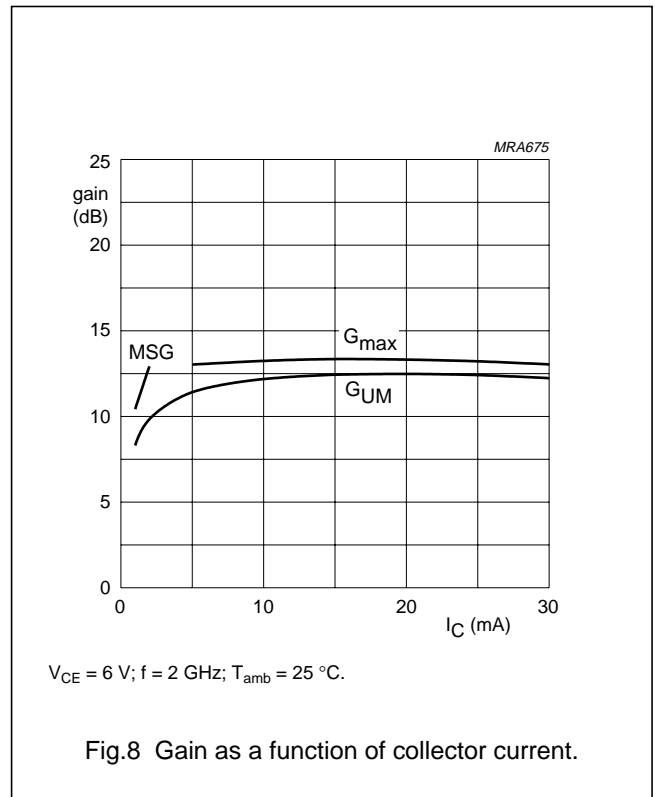
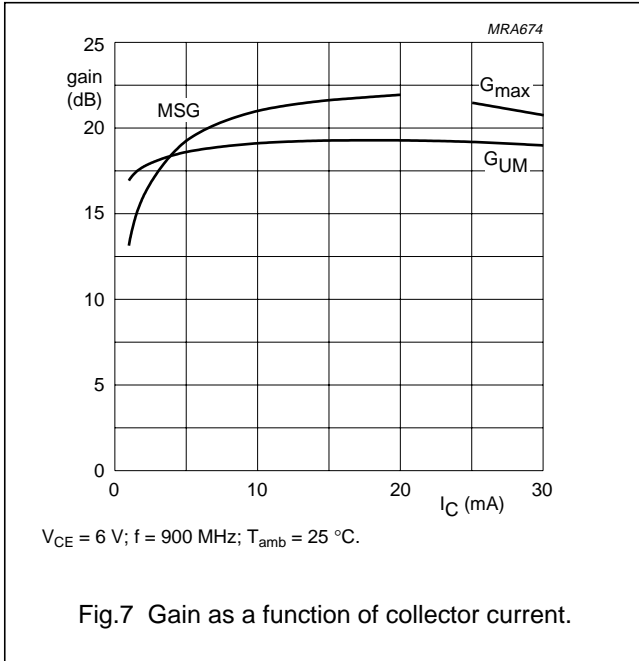
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In Figs 7 to 10, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



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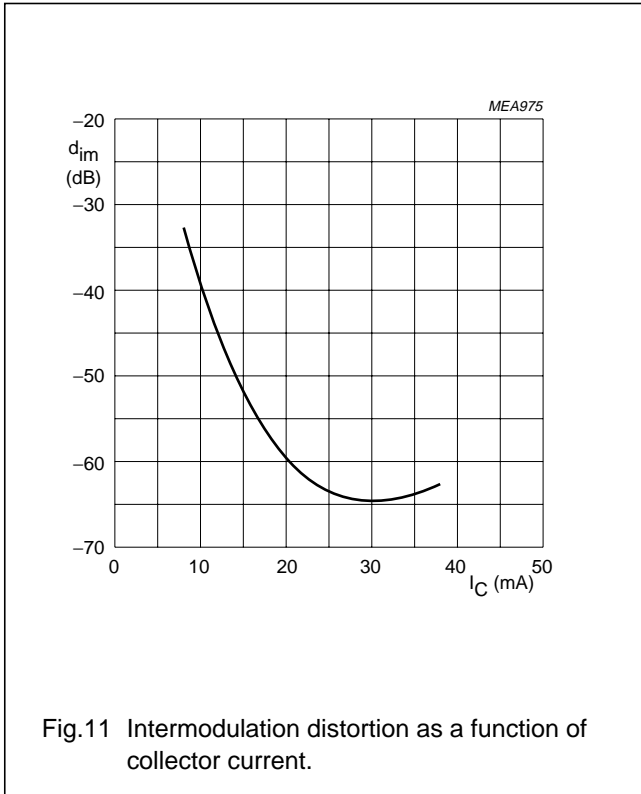


Fig.11 Intermodulation distortion as a function of collector current.

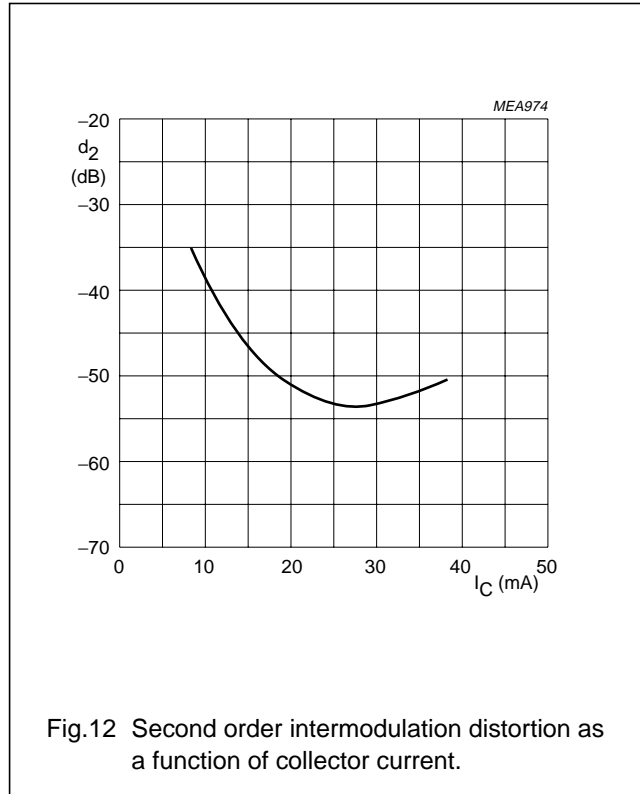
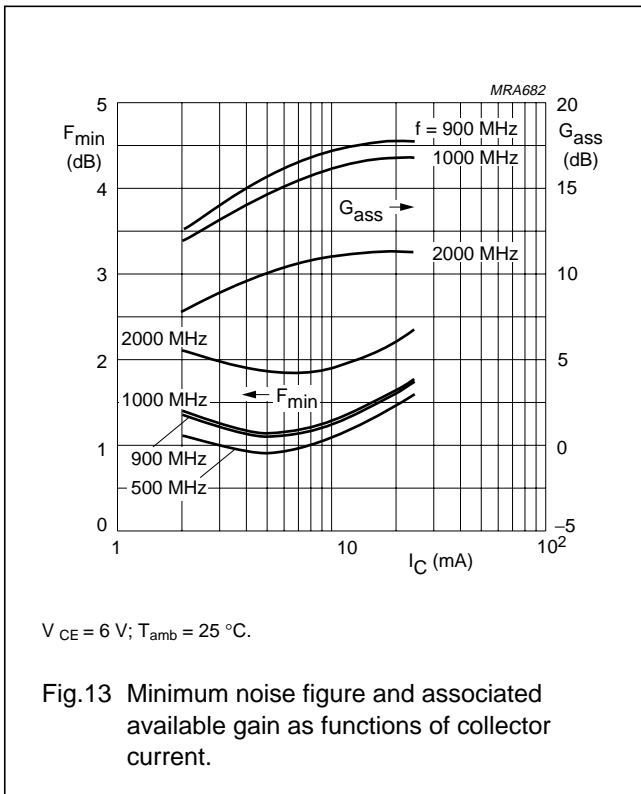
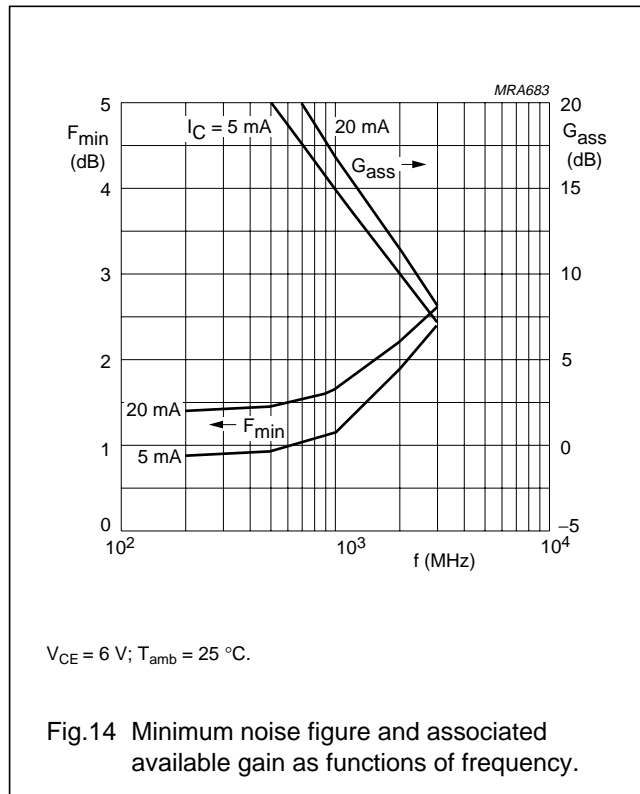


Fig.12 Second order intermodulation distortion as a function of collector current.



$V_{CE} = 6\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}.$

Fig.13 Minimum noise figure and associated available gain as functions of collector current.

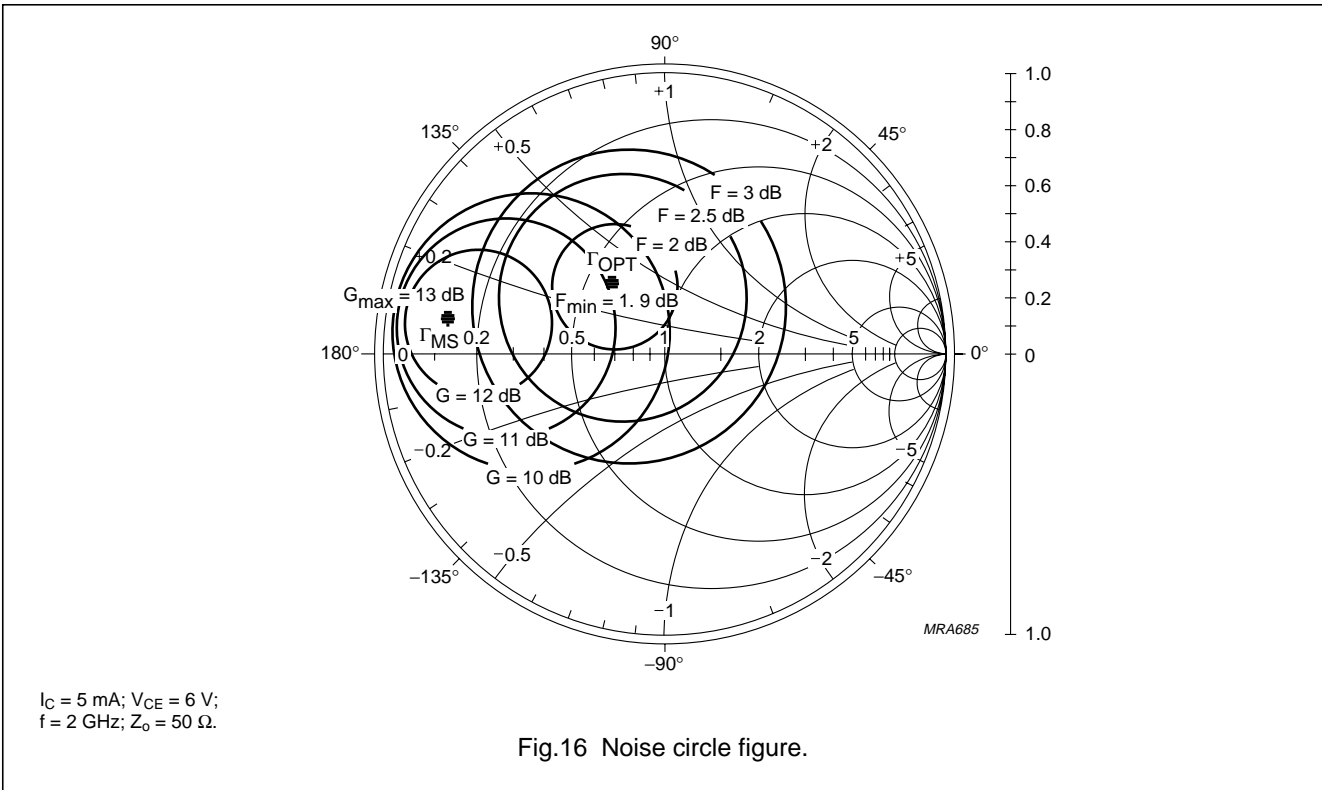
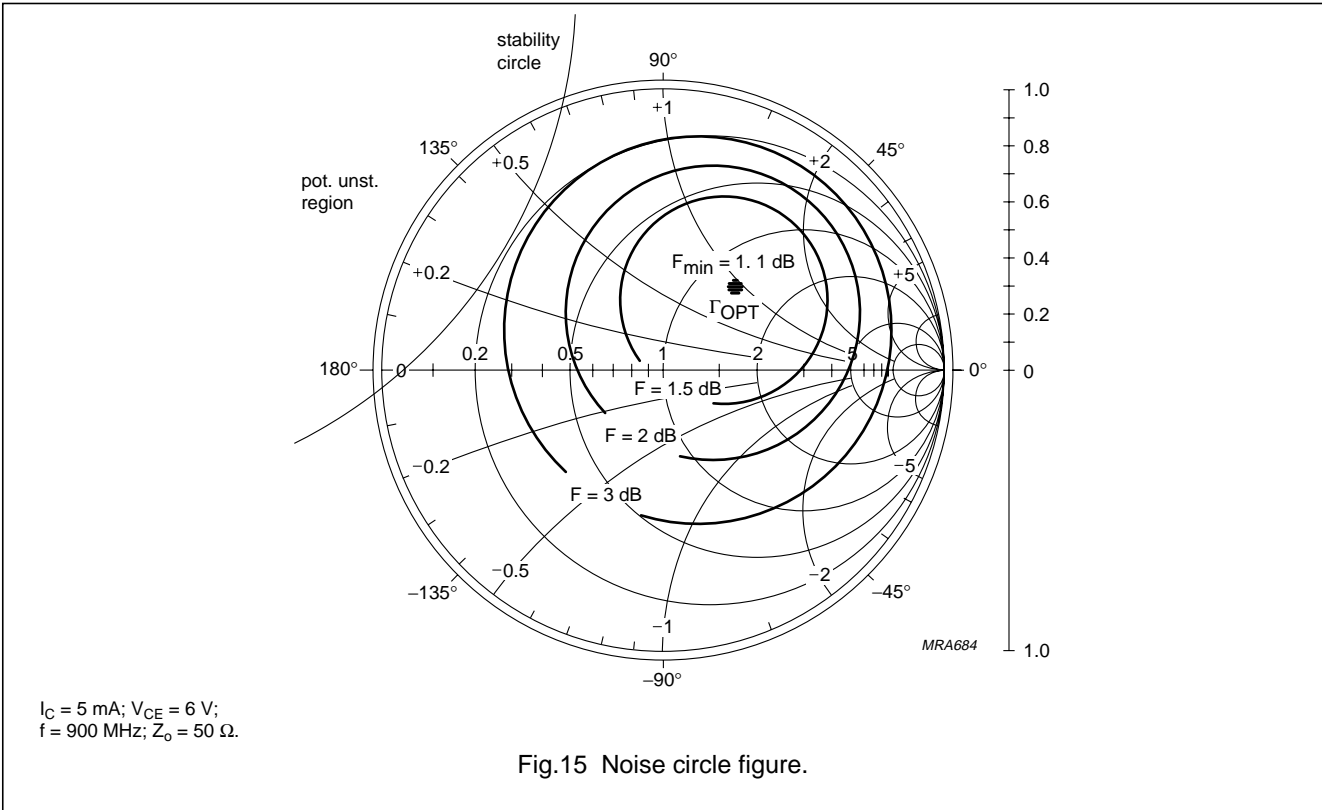


$V_{CE} = 6\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}.$

Fig.14 Minimum noise figure and associated available gain as functions of frequency.

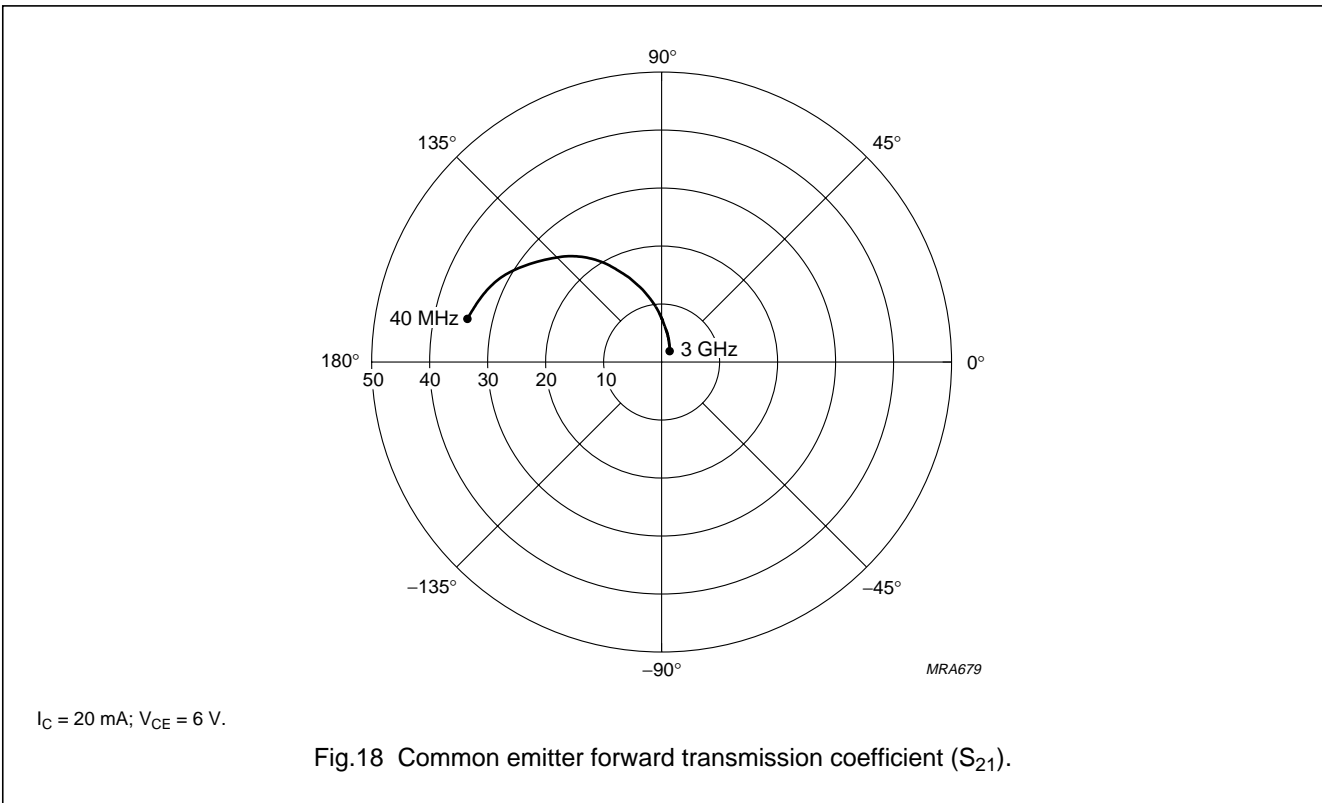
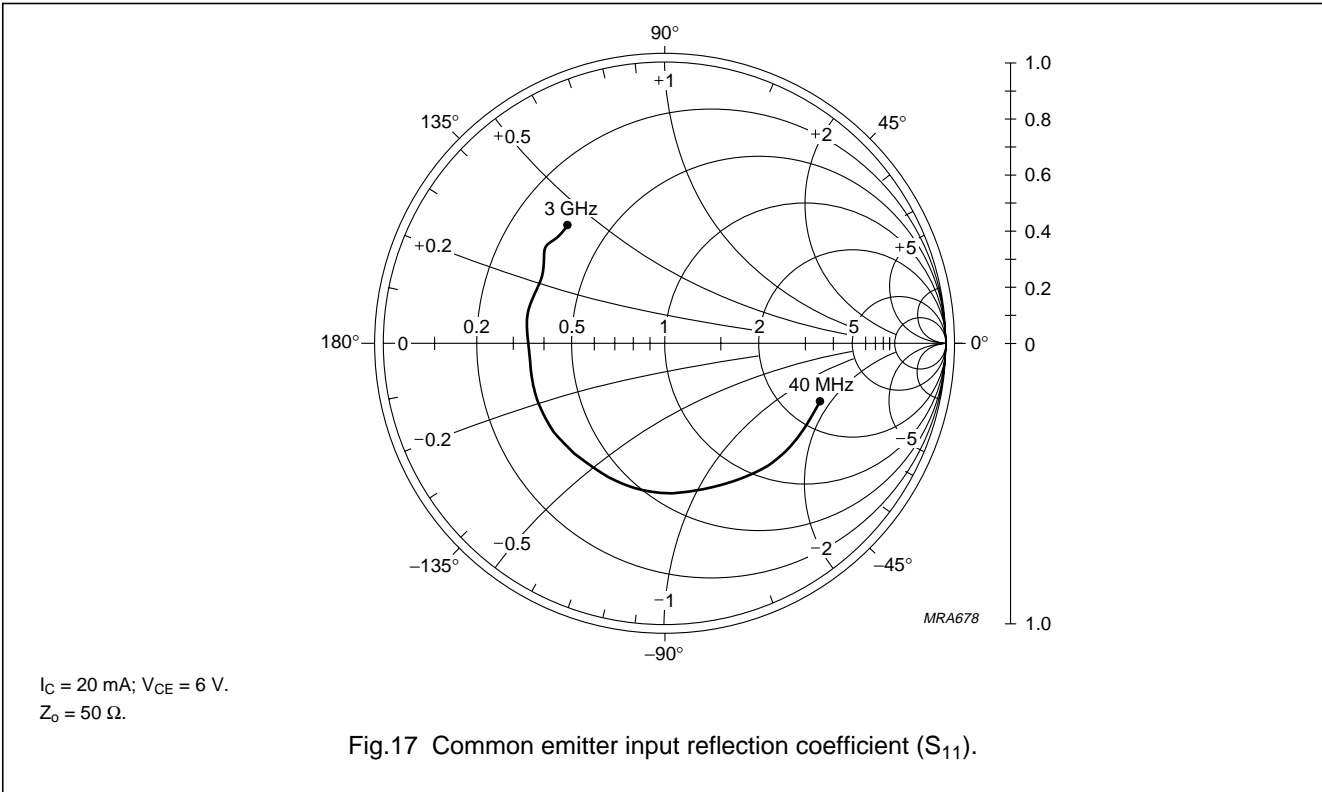
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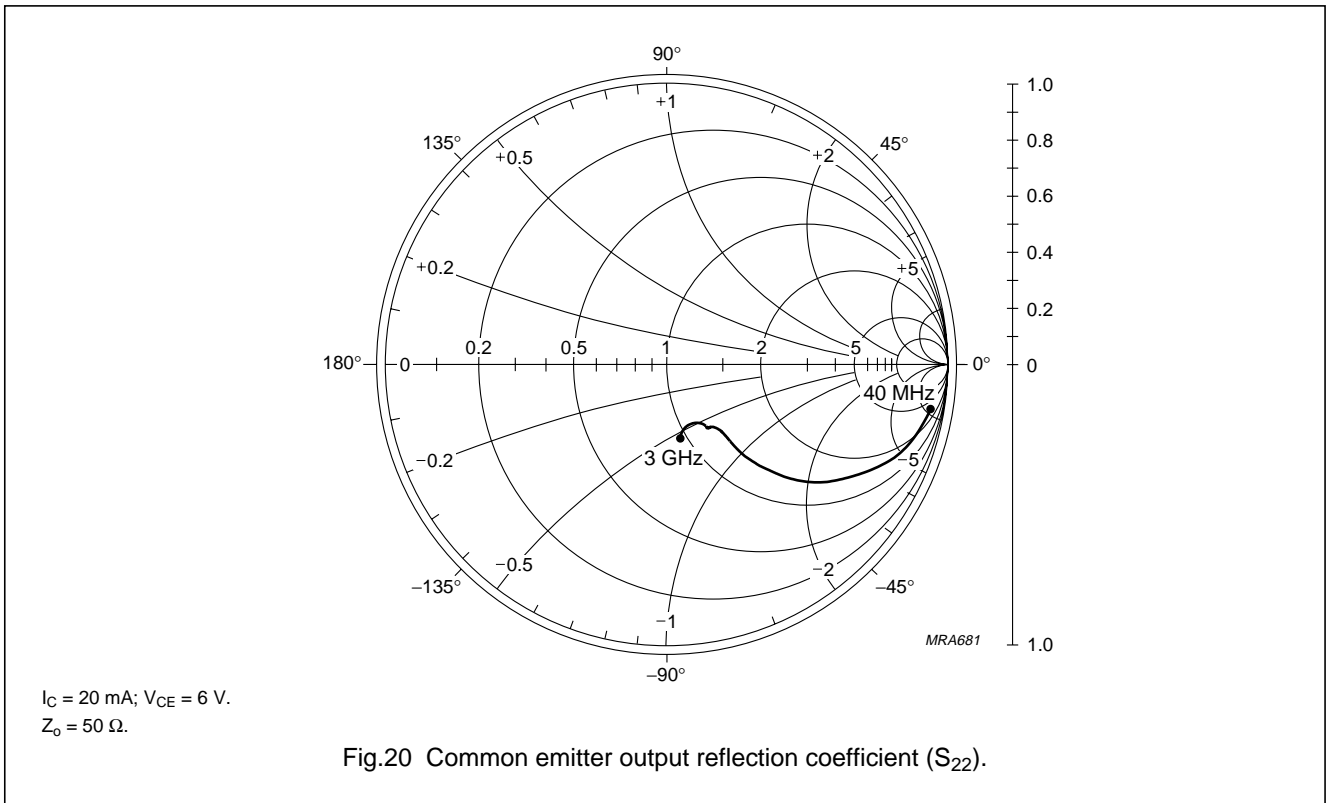
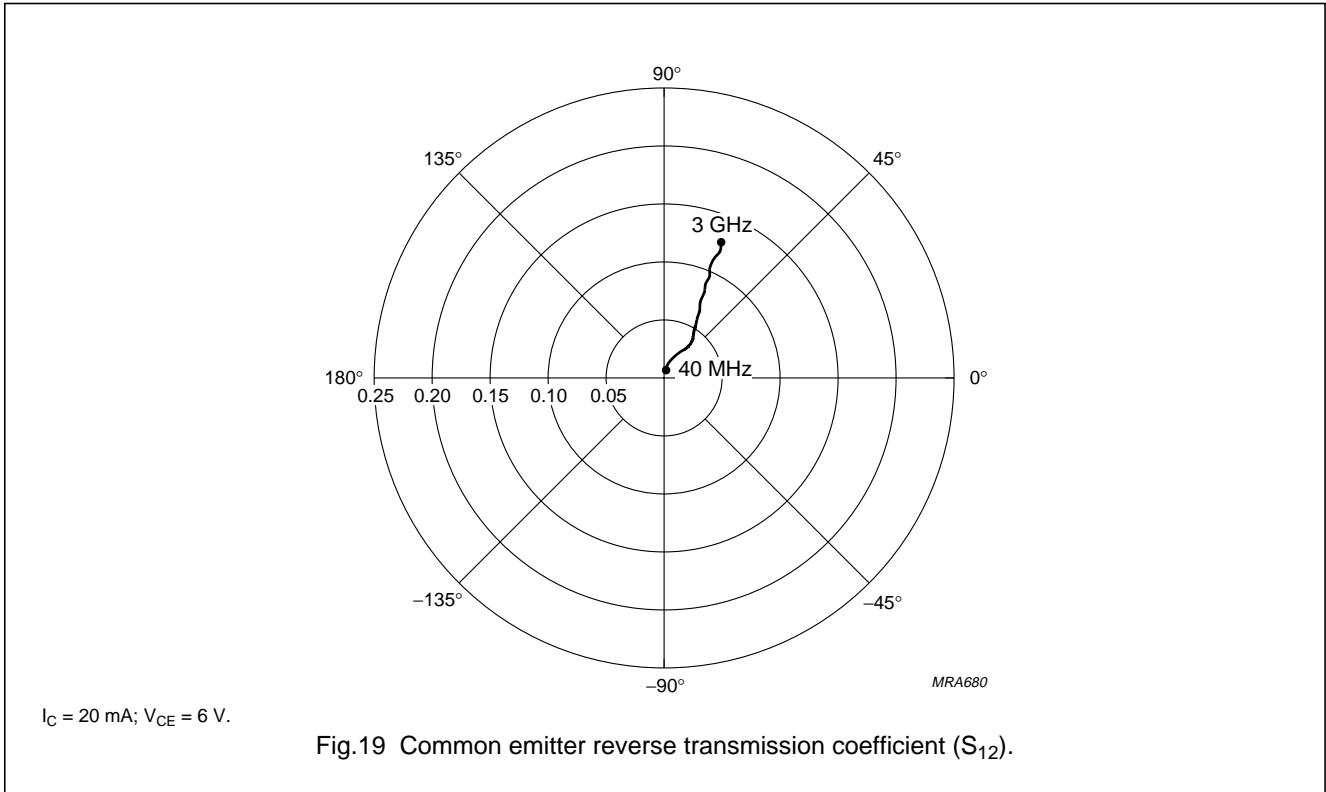
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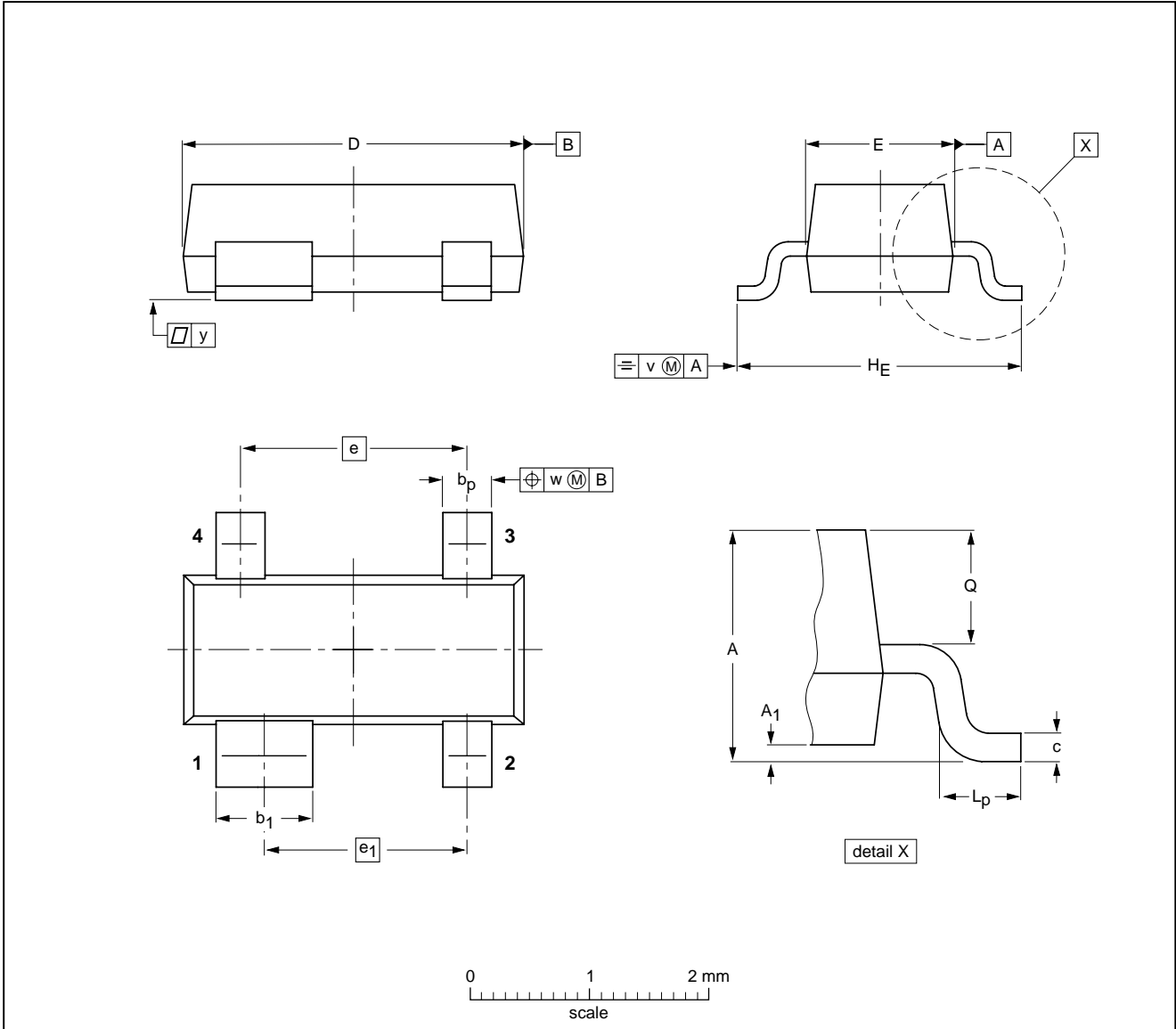
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PACKAGE OUTLINES

Plastic surface mounted package; 4 leads

SOT143B



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

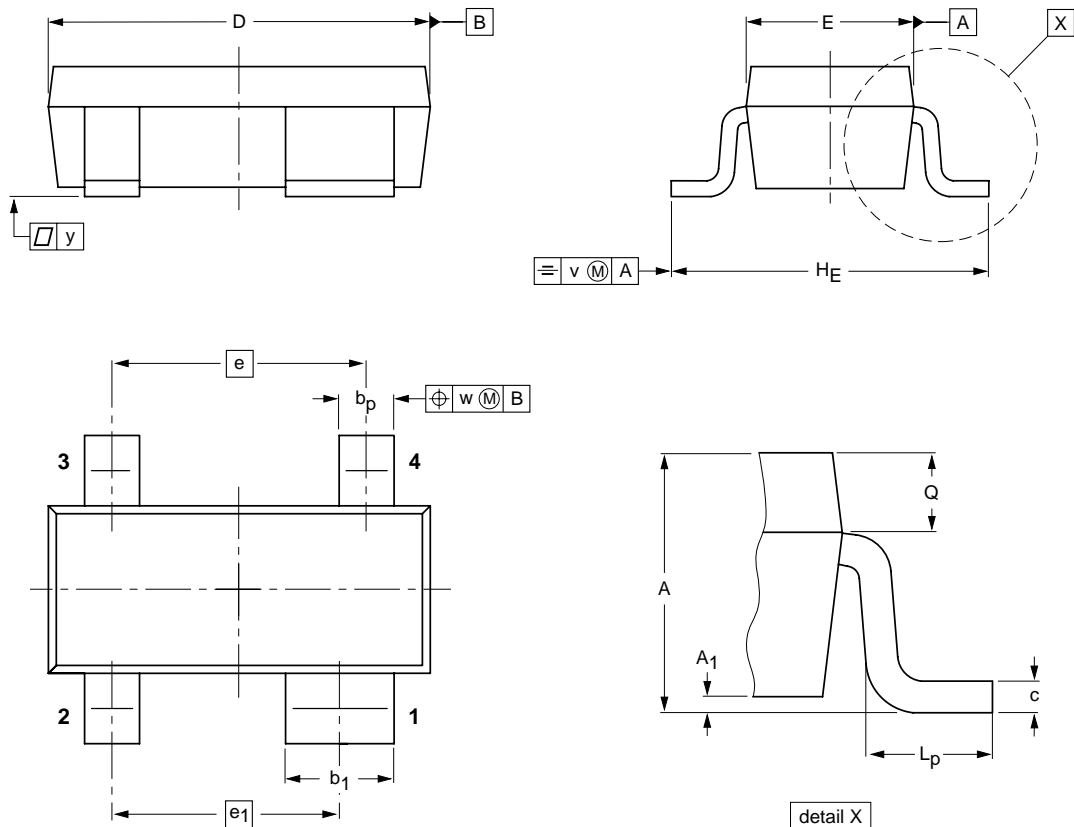
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

NPN 9 GHz wideband transistor

BFG520; BFG520/X; BFG520/XR

Plastic surface mounted package; reverse pinning; 4 leads

SOT143R



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.55 0.25	0.45 0.25	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143R						97-03-10